



STC5NF30V

N-channel 30V - 0.027Ω - 5A - TSSOP8
2.7V-drive STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STC5NF30V	30V	< 0.031 Ω (@ 4.5 V) < 0.035 Ω (@ 2.7 V)	5A

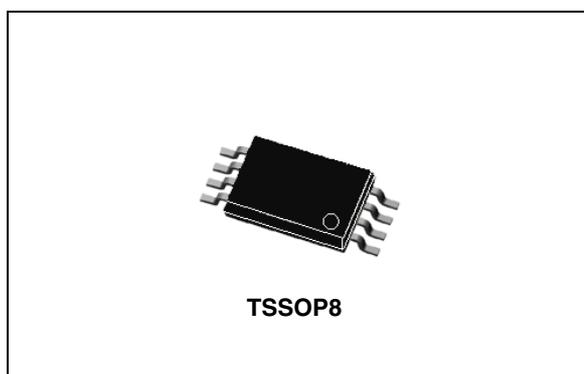
- Ultra low threshold gate drive (2.7V)
- Standard outline for easy automated surface mount assembly

Description

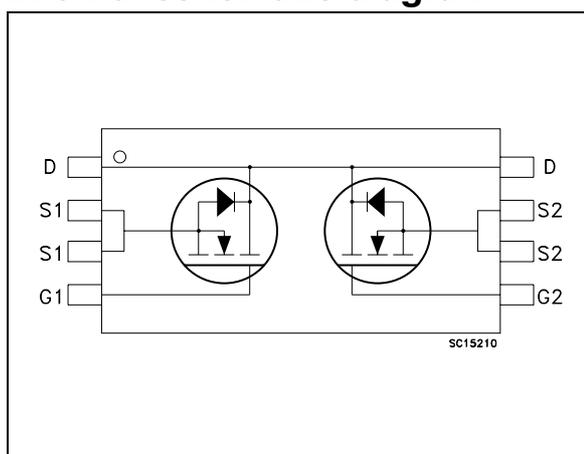
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STC5NF30V	C5NF30V	TSSOP8	

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuit	8
4	Package mechanical data	9
5	Revision history	11

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	30	V
V_{DGR}	Drain-gate voltage ($R_{GS} = 20K\Omega$)	20	V
V_{GS}	Gate-source voltage	± 12	V
I_D	Drain current (continuous) at $T_C = 25^\circ C$	5	A
I_D	Drain current (continuous) at $T_C = 100^\circ C$	3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	20	A
P_{TOT}	Total dissipation at $T_C = 25^\circ C$	1.5	W
T_{stg}	Storage temperature	-55 to 150	$^\circ C$
T_J	Max. operating junction temperature	-55 to 150	$^\circ C$

1. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thJ-PBC}$	Thermal resistance junction-PBC Max	100 ⁽¹⁾	$^\circ C/W$
$R_{thJ-PBC}$	Thermal resistance junction-PBC Max	83.5 ⁽²⁾	$^\circ C/W$

1. When Mounted on FR-4 board with 1 inch² pad, 2 oz of Cu and t = 10 sec

2. When Mounted on minimum recommended footprint

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu A, V_{GS} = 0$	30			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating} @ 125^{\circ}C$			1 10	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 12V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.6			V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 4.5V, I_D = 2.5A$ $V_{GS} = 2.7V, I_D = 2.5A$		0.027 0.031	0.031 0.035	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 2.5A$		9.5		S
C_{iss}	Input capacitance	$V_{DS} = 15V, f = 1\text{ MHz},$ $V_{GS} = 0$		460		pF
C_{oss}	Output capacitance			200		pF
C_{rss}	Reverse transfer capacitance			50		pF
Q_g	Total gate charge	$V_{DD} = 16V, I_D = 4.5A$		8.5	11.5	nC
Q_{gs}	Gate-source charge	$V_{GS} = 4.5V$		1.8		nC
Q_{gd}	Gate-drain charge	Figure 15 on page 8		2.4		nC

1. Pulsed: pulse duration=300 μs , duty cycle 1.5%

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 10V, I_D = 2.5A,$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ Figure 13 on page 8		7		ns
t_r	Rise time			33		ns
$t_{d(off)}$	Turn-off delay time			27		ns
t_f	Fall time			10		ns
$t_{d(off)}$	Off-voltage rise time	$V_{clamp} = 16V, I_D = 5A$ $R_G = 4.7\Omega, V_{GS} = 4.5V$ Figure 15 on page 8		26		ns
t_f	Fall time			11		ns
t_c	Cross-over time			21		ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				20	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 5A, V_{GS} = 0$			1.2	V
t_{rr}	Reverse recovery time	$I_{SD} = 5A,$ $di/dt = 100A/\mu s,$ $V_{DD} = 10V, T_J = 150^\circ C$ <i>Figure 15 on page 8</i>		26		ns
Q_{rr}	Reverse recovery charge			13		μC
I_{RRM}	Reverse recovery current			1		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

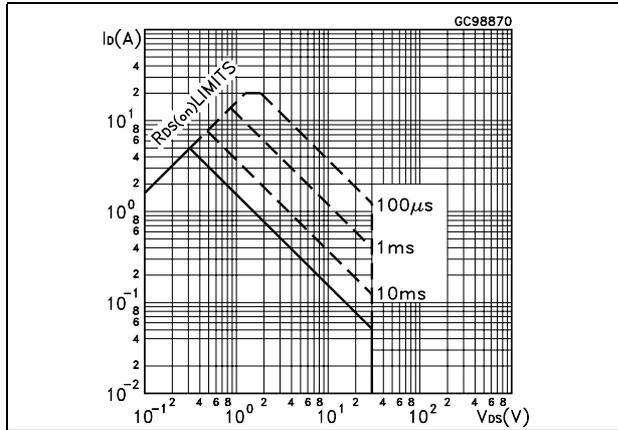


Figure 2. Thermal impedance

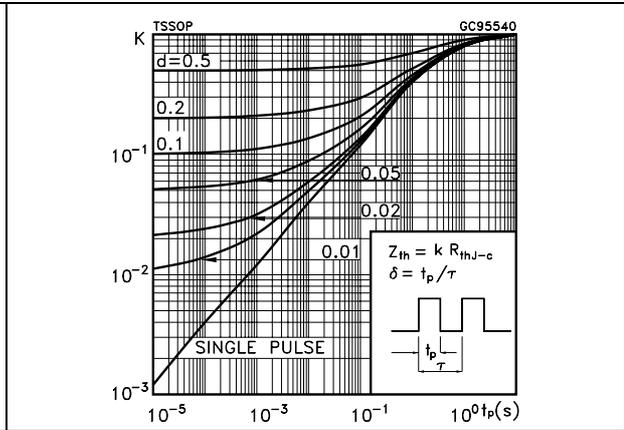


Figure 3. Output characteristics

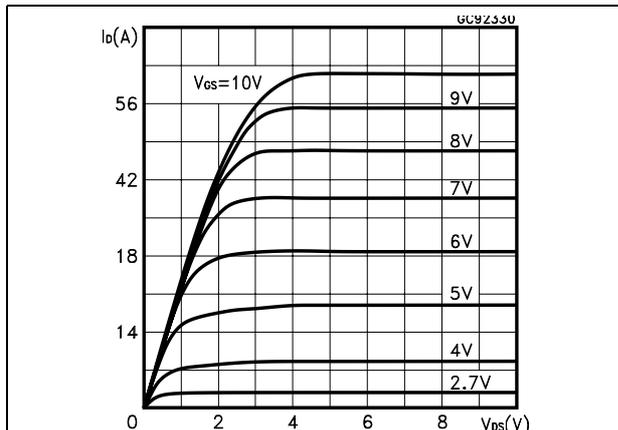


Figure 4. Transfer characteristics

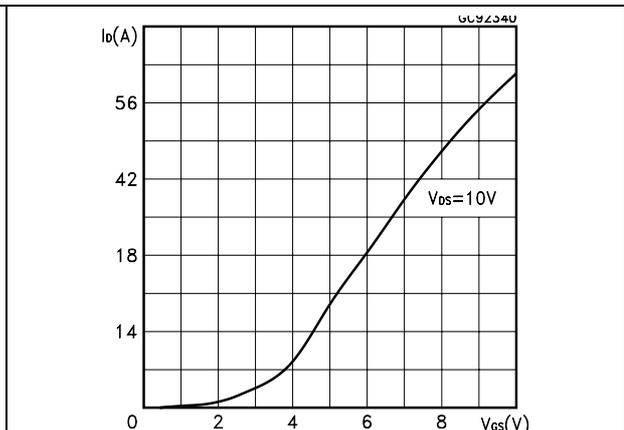


Figure 5. Transconductance

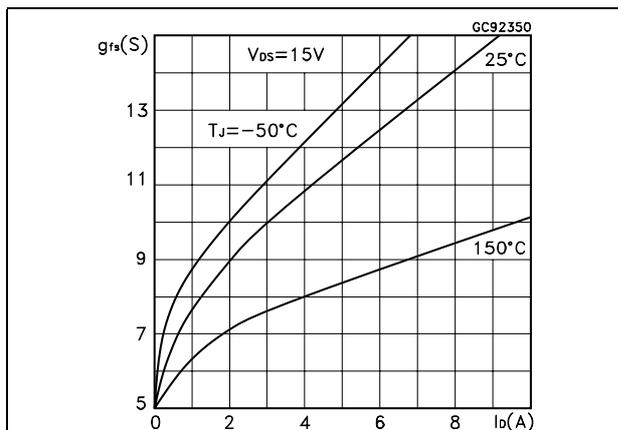


Figure 6. Static drain-source on resistance

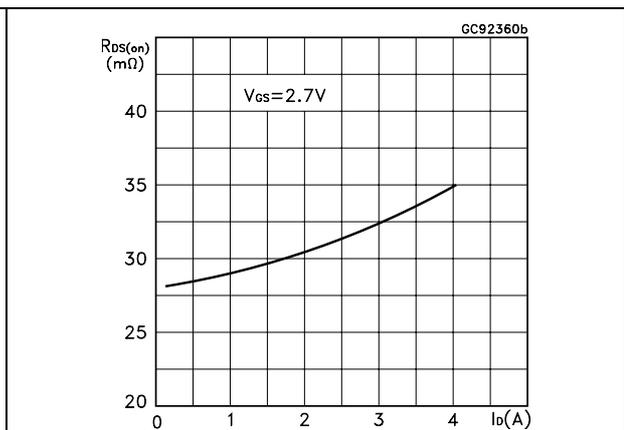


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

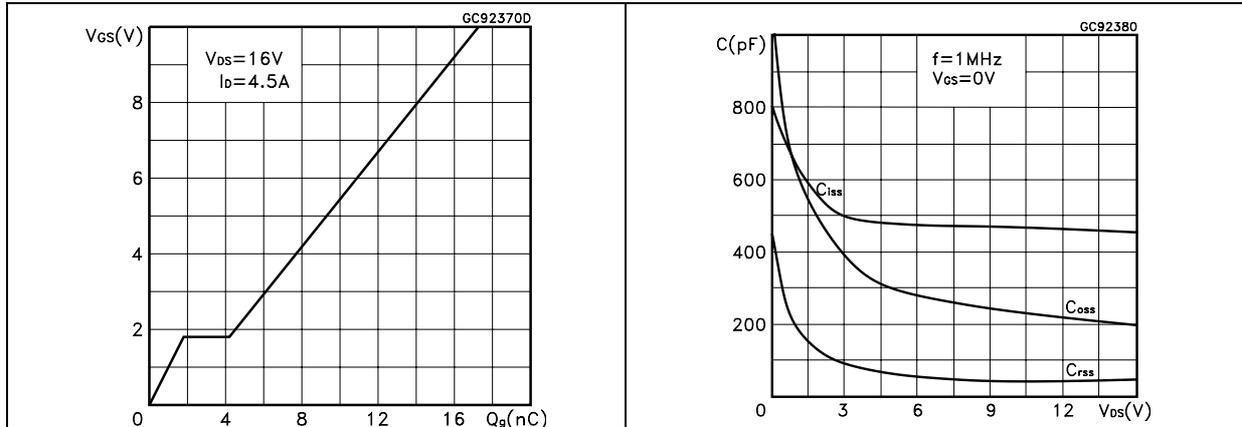


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

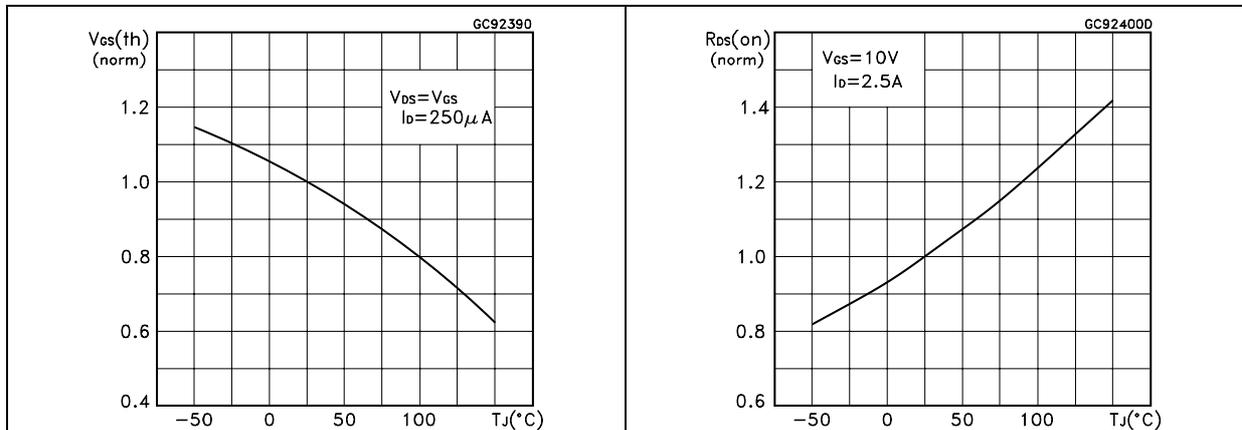
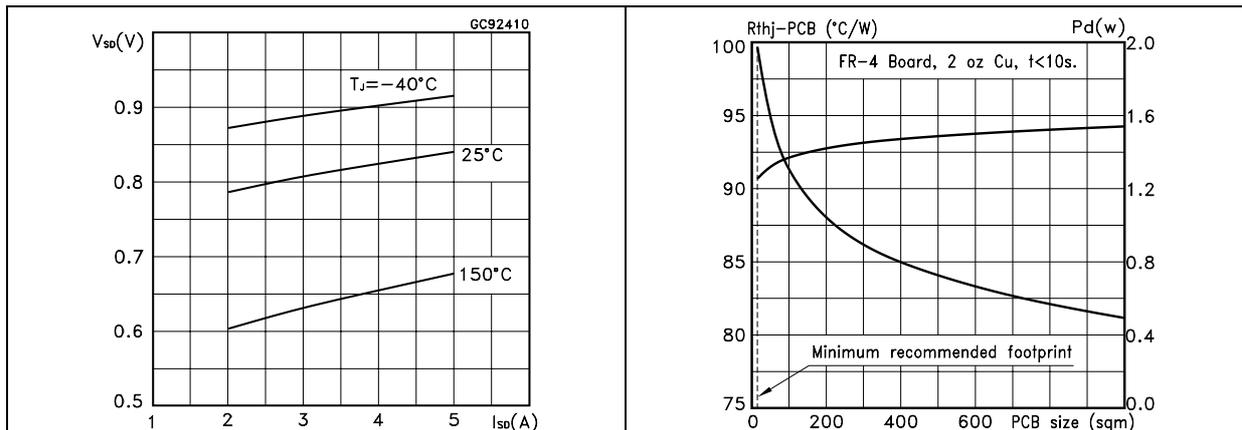


Figure 11. Source-drain diode forward characteristics Figure 12. Thermal resistance and max power



3 Test circuit

Figure 13. Switching times test circuit for resistive load

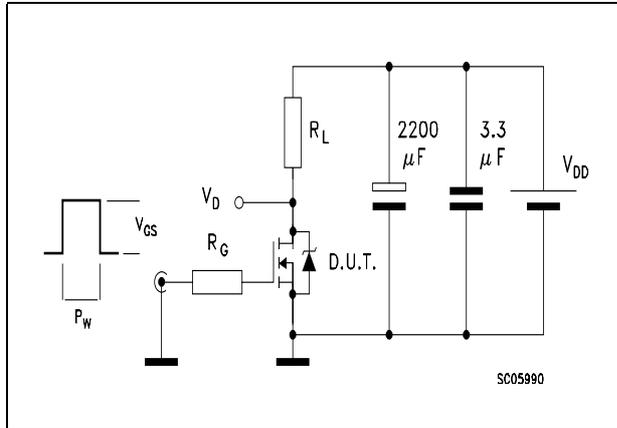


Figure 14. Gate charge test circuit

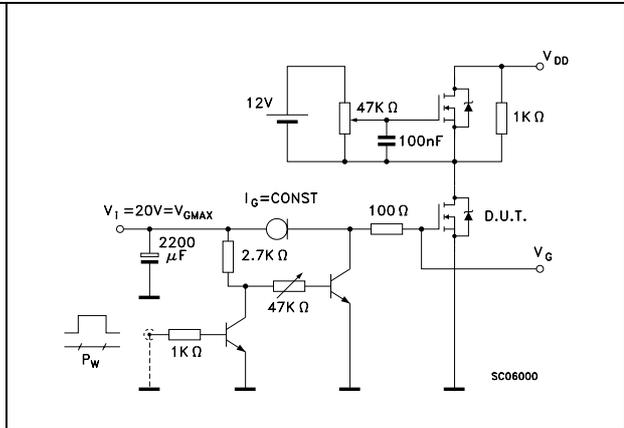


Figure 15. Test circuit for inductive load switching and diode recovery times

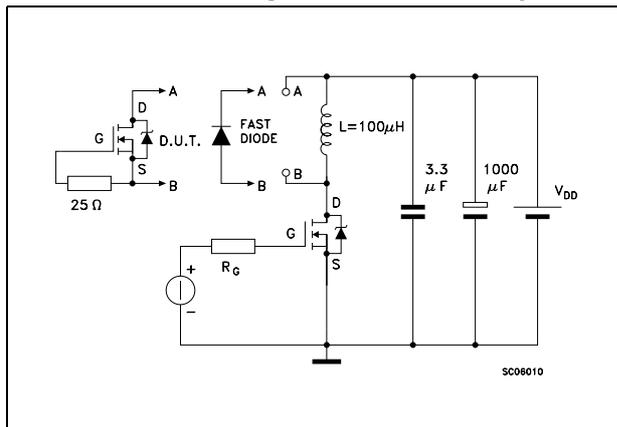


Figure 16. Unclamped Inductive load test circuit

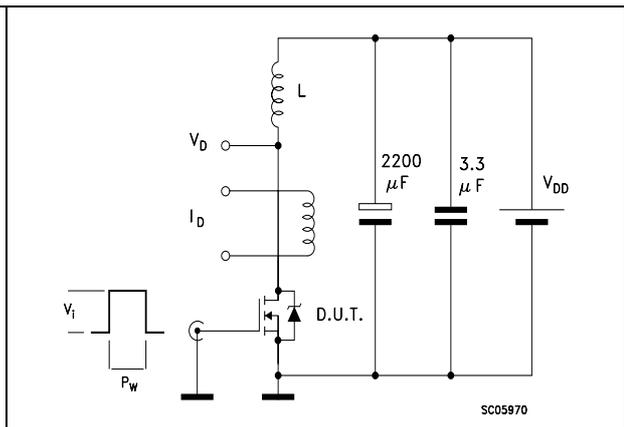
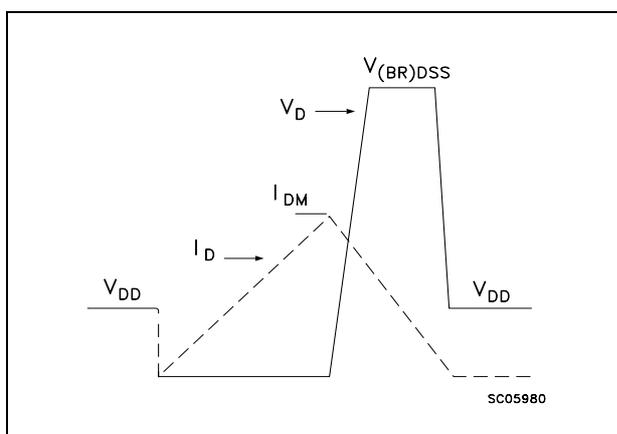


Figure 17. Unclamped inductive waveform

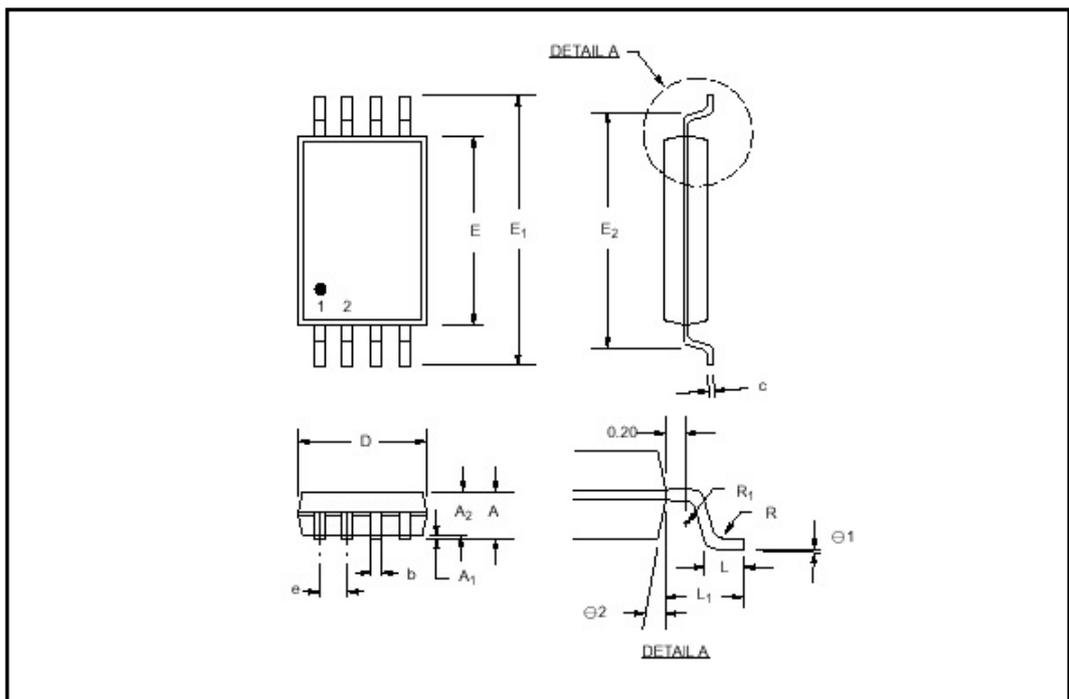


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TSSOP8 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	1.05		1.20	0.041		0.047
A1	0.05		0.15	0.002		0.006
A2	0.80		1.05	0.032		0.041
b	0.19		0.30	0.008		0.012
c		0.127			0.005	
D	2.90		3.10	0.114		0.122
E	4.30		4.50	0.170		0.177
E1	6.20		6.60	0.240		0.260
E2	5.14		5.24	0.202		0.206
e		0.65			0.025	
L	0.45		0.75	0.018		0.030
L1	0.90		1.10	0.0355		0.0433
R	0.09			0.004		
R1	0.09			0.004		
θ1	0°		8°	0°		8°
θ2	12°					



5 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	1	First release
08-Aug-2006	2	New template, SOA updated

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